



<b>Form PTO-1449 (modified)</b> <b>List of Patents and Publications</b> <b>For Applicant's Information</b> <b>Disclosure Statement</b> <b>(Use several sheets if necessary)</b>			ATTY. DOCKET NO: 5310-03000		SERIAL NO: 09/744,877		
			APPLICANT: Halimaoui et al.		CONFIRMATION NO.: 8711		
			FILING DATE: January 29, 2001		ART UNIT: 2822		
<b>U.S. PATENT DOCUMENTS</b>							
EXAM. INITIALS	REF. DES	DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
CK	A1	5,021,354	6/1991	Pfiester			
CK	A2	5,106,768	8/1998	Kuo			
<b>FOREIGN PATENT DOCUMENTS</b>							
EXAM. INITIALS	REF. DES	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUB CLASS	TRANSLATION YES/NO
CK	A3	JP 61016530	1/1986	JP			Abstract
CK	A4	WO 97 41593	11/1997	WO			
<b>OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)</b>							
CK	A5	Soleimani et al.; "Formation of Ultrathin Nitrided SiO <sub>2</sub> Oxides by Direct Nitrogen Implantation into Silicon"; <i>J. Electrochem. Soc.</i> , 1995, 42(10).					

EXAMINER: Christy Swacek

DATE CONSIDERED: 2/20/04

**EXAMINER:** Initial if citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to the patent owner.